

# Search History. 10/20/04. ~~10/19/04~~ (5 pp.)

L Number	Hits	Search Text	DB	Time stamp
1	2890	((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.	USPAT; US-PGPUB	2004/10/19 08:37
2	3	((((257/288) or (257/408) or (257/409) or (257/410) or (257/411) or (438/230)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/19 08:38
-	244	(nitridization nitride nitriding nitridizing) near4 (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 07:41
-	18	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) near6 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:01
-	1	(nitridization nitride nitriding nitridizing) near6 (ald atomic adj layer adj deposition) and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:02
-	179	(nitridization nitride nitriding nitridizing) and silicon adj nitride and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:03
-	96	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:03
-	4	(nitridization nitride nitriding nitridizing) and silicon adj nitride and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:05
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3 N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:06
-	4	(nitridization nitride nitriding nitridizing) and ("Si.sub.3\$1N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:06
-	4	("Si.sub.3\$1" N.sub.4" silicon adj nitride) and (spacer barrier) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:06
-	5	("Si.sub.3\$1" N.sub.4" silicon adj nitride) and ("without" near3 (ammonia "NH.sub.3")) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:07
-	171	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/17 15:08

	2	(ald atomic adj layer adj deposition).ti,ab,clm. and silicon adj nitride.ti,ab,clm. and ("without" near4 (ammonia "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:10
	31	pdf adj solutions.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:10
	0	pdf adj solutions.as. and nitride.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:21
	2691	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.	USPAT; US-PGPUB	2004/10/19 08:37
	3	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/19 08:38
	1	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and "without" near3 (ammonia "NH.sub.3") and (lightly adj doped adj drain lightly-doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:26
	5	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (ald atomic adj layer adj deposition) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\\$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:36
	0	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and (nitride near4 ("without" near4 (ammonia "NH.sub.3")))) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\\$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:37
	1	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\\$1"N.sub.4" SiN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:42
	0	((257/288) or (257/408) or (257/409) or (257/410) or (257/411)).CCLS.) and ("without" near4 (ammonia "NH.sub.3")) and (ldd lightly adj doped adj drain) and (silicon adj nitride "Si.sub.3"\\$1"N.sub.4" SiN) and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:49
	0	(NO-nitridi?ation "N.sub.2"\\$10-nitridi?ation) and silicon adj nitride and (roxnox ono oxide-nitride-oxide "oxide/nitride/oxide") and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:52
	0	(NO-nitridi?ation "N.sub.2"\\$10-nitridi?ation) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 15:52
	4	((NO "N.sub.2"\\$10) near3 nitridi?ation) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:00
	0	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo\\$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4") and (ono roxnox oxide-nitride-oxide )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:03

	12	(atomic adj layer adj deposition ald pecvd plasma adj enhanced adj chemical adj vapo\$r adj deposition) near5 "N.sub.2" near5 ("SiCl.sub.4" "SiF.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:08
	282	method near6 ono.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:09
	0	method near6 ono.clm. and silicon adj nitride and (nitridization nitridisation) near4 (ald atomic adj layer adj deposition pecvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:10
	207	method near6 ono.clm. and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:10
	22	method near6 ono.clm. and silicon adj nitride and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:13
	1	method near6 ono.clm. and silicon adj nitride and ("SiF.sub.4" "SiCl.sub.4") and (lightly adj doped adj drain ldd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:21
	13	penetration near4 nitrogen and (ono roxnox oxide-nitride-oxide) and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:52
	1	N-containing adj gas and silicon adj nitride and spacer and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:56
	1	N-containing adj gas and silicon adj nitride and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:56
	8	N-containing adj gas and silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:57
	311	method near3 (ono oxide-nitride-oxide roxnox)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 16:58
	137	method near3 (ono oxide-nitride-oxide roxnox).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:18
	85	(oxide-nitride-oxide ono roxnox) and (ldd lightly adj doped adj drain) and spacer and etch adj stop	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:27
	8	etch adj stop adj layer near3 silicon adj nitride and silicon adj nitride near4 barrier and (ldd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 17:56

	112	(lhd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/\$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:00
	0	(lhd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/\$9.ccls. and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:01
	17	(lhd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/\$9.ccls. and (ald atomic adj layer adj deposition pecvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:01
	17	(lhd lightly adj doped adj drain).ti,ab,clm. and silicon adj nitride and ono and 438/\$9.ccls. and (ald atomic adj layer adj deposition pecvd plasma adj enhanced adj chamical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/17 18:02
	1	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer and (lhd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:46
	4	double near4 silicon adj nitride and (ono roxnox oxide-nitride-oxide) and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:47
	84	method near4 silicon adj nitride near4 spacer and (lhd lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 07:51
	3	method near4 silicon adj nitride near4 spacer and (lhd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:25
	3	(method near4 silicon adj nitride near4 spacer and (lhd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide NO "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:28
	0	(method near4 silicon adj nitride near4 spacer and (lhd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:29
	0	(method near4 nitridization and (lhd lightly adj doped adj drain) and (ald atomic adj layer adj deposition)) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:29
	0	(method near4 nitridization) and (lhd lightly adj doped adj drain) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30
	0	(method near4 nitridization) and (ald atomic adj layer adj deposition) and (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30
	0	(method near4 nitridization) near6 (nitride adj oxide "N.sub.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:30

-	0	method near4 nitridization and ("no" adj2 ammonia)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 08:31
-	47	method near4 nitridization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 08:31
-	14	(method near4 nitridization).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 08:31
-	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 08:32
-	3	((method near4 nitridization).ti,ab,clm.) not (ammonia "NH.sub.3") and method near4 nitridization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 08:36
-	16	(US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or US-6744098-\$ or US-6649543-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-6686298-\$ or US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or US-20020137296-\$ or US-20040042307-\$).did.	USPAT; US-PGPUB	2004/10/18 09:17
-	0	((US-6756634-\$ or US-6436848-\$ or US-5674788-\$ or US-6690046-\$ or US-6744098-\$ or US-6649543-\$ or US-6323519-\$ or US-6653184-\$ or US-6682979-\$ or US-6686298-\$ or US-5734185-\$).did. or (US-20040146644-\$ or US-20040137742-\$ or US-20030143792-\$ or US-20020137296-\$ or US-20040042307-\$).did.) and fu.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 09:36
-	27	ild and spacer and silicon adj nitride and ono and ild	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 10:16
-	28	ild near4 protect\$3 and gate and silicon adj nitride and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 10:16
-	2	("20020146879").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 15:19